ETR0202_002

Voltage Detectors, Delay Circuit Built-In

GENERAL DESCRIPTION

The XC61F series are highly accurate, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies. A delay circuit is built-in to each detector.

Detect voltage is extremely accurate with minimal temperature drift.

Both CMOS and N-channel open drain output configurations are available.

Since the delay circuit is built-in, peripherals are unnecessary and high density mounting is possible.

APPLICATIONS

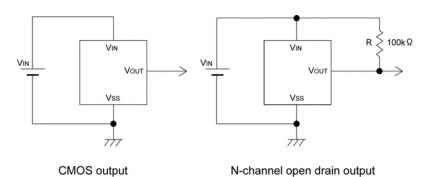
Microprocessor reset circuitry Memory battery back-up circuits Power-on reset circuits Power failure detection System battery life and charge voltage monitors Delay circuitry

FEATURES

Highly Accurate	: ± 2%
Low Power Consumption	: 1.0 µ A(TYP.)[VIN=2.0V]
Detect Voltage Range	: 1.6V ~ 6.0V in 0.1V increments
Operating Voltage Range	: 0.7V ~ 10.0V
Detect Voltage Temperat	ture Characteristics
	: ± 100ppm/ (TYP.)
Built-In Delay Circuit	: 1ms ~ 50ms
	50ms ~ 200ms
	80ms ~ 400ms
Output Configuration	: N-channel open drain or CMOS
Small Packages	: SOT-23 (250mW)
	: SOT-89 (500mW)
	: TO-92 (300mW)

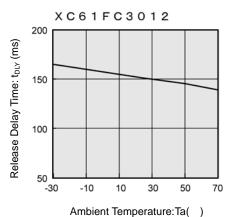
* No parts are available with an accuracy of $\pm 1\%$

TYPICAL APPLICATION CIRCUITS

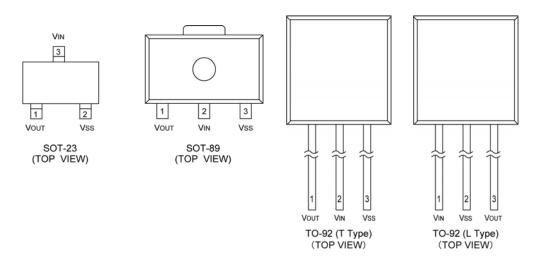


TYPICAL PERFORMANCE CHARACTERISTICS

Release Delay Time vs. Ambient Temperature



PIN CONFIGURATION



PIN ASSIGNMENT

	PIN NUMBER			PIN NAME	FUNCTION
SOT-23	SOT-89	TO-92 (T)	TO-92 (L)		FUNCTION
3	2	2	1	Vin	Supply Voltage Input
2	3	3	2	Vss	Ground
1	1	1	3	Vout	Output

PRODUCT CLASSIFICATION

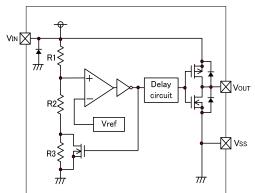
Ordering Information

XC61F

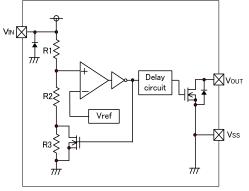
DESIGNATOR	DESCRIPTION	SYMBOL	DESCRIPTION
	Output Configuration	С	: CMOS output
	Output Configuration	N	: N-ch open drain output
	Detect Voltage	16 ~ 60	: e.g. 2.5V 2 , 5
	Delect vollage	10 ~ 00	: e.g. 3.8V 3, 8
		1	: 50ms ~ 200ms
	Release Output Delay	4	: 80ms ~ 400ms
		5	: 1ms ~ 50ms
	Detect Accuracy	2	: Within ± 2.0%
		М	: SOT-23
	Deskere	Р	: SOT-89
	Package	Т	: TO-92 (Standard)
		L	: TO-92 (Custom pin configuration) (Discontinued Product)
		R	: Embossed tape, standard feed
	Device Orientation	L	: Embossed tape, reverse feed
		Н	: Paper type (TO-92)
		В	: Bag (TO-92)

BLOCK DIAGRAMS

(1) CMOS output



(2) N-channel open drain output



ABSOLUTE MAXIMUM RATINGS

PARAMETER		RATINGS	UNITS	
ge	Vin	12.0	V	
ent	Ιουτ	50	mA	
CMOS	Vour	Vss -0.3 ~ VIN + 0.3	V	
N-ch open drain	V001	Vss -0.3 ~ 9	v	
SOT-23		250		
SOT-89	Pd	500	mW	
TO-92		300		
ture Range	Topr	-30 ~ +85		
ure Range	Tstg	-40 ~ +125		
	ge ent CMOS N-ch open drain SOT-23 SOT-89 TO-92 ture Range	ge VIN ent IOUT CMOS VOUT N-ch open drain SOT-23 SOT-89 Pd TO-92 ture Range Topr	ge VIN 12.0 ent Iout 50 CMOS Vout Vss-0.3 ~ Vin + 0.3 N-ch open drain Vout Vss - 0.3 ~ 9 SOT-23 Pd 250 SOT-89 Pd 500 TO-92 Topr -30~+85	

ELECTRICAL CHARACTERISTICS

Ta = 25

PARA	METER	SYMBOL	CONDITIO	ONS	MIN.	TYP.	MAX.	UNITS	CIRCUIT	
Detect	Voltage	Vdf			VDF(T)	VDF(T)	VDF(T)	V		
Deleci	vollage	VDF			x 0.98		x 1.02	v		
Hystores	sis Width	VHYS			Vdf	Vdf	Vdf	V		
Trysteres		VIIIS			x 0.02	x 0.05	x 0.08	v		
				VIN = 1.5V	-	0.9	2.6			
				VIN = 2.0V	-	1.0	3.0			
Supply	Current	lss		VIN = 3.0V	-	1.3	3.4	μΑ		
				VIN = 4.0V	-	1.6	3.8			
				VIN = 5.0V	-	2.0	4.2			
Operatin	g Voltage	Vin	VDF= 1.6V te	o 6.0V	0.7	-	10.0	V		
				VIN = 1.0V	1.0	2.2	-			
		VIN = 2.0	VIN = 2.0V	3.0	7.7	-				
			N-ch VDS =0.5V	VIN = 3.0V	5.0	10.1	-			
Output	Current IOUT	Ιουτ		VIN = 4.0V	6.0	11.5	-	mA		
				-			VIN = 5.0V	7.0	13.0	-
			P-ch VDS=2.1V (CMOS Output) VIN = 8.0V		-	-10.0	-2.0			
Leak	CMOS Output	lleak		10.01/	-	0.01	-			
Current	Nch Open Drain	lieak	V_{IN} = 10.0V , V_{OUT} = 10.0V		-	0.01	0.1	μA		
Tempe	Voltage erature tteristics	VDF Topr• VDF			-	± 100	-	ppm/	-	
Release	Delay Time		VIN changes from 0.6V to 10V		50	-	200			
	Delay Time TDLY*	TDLY*			80		400	ms		
					1		50			

VDF (T): Setting detect voltage value Release Voltage: VDR = VDF + VHYS

* Release Delay Time: 1ms to 50ms & 80ms to 400ms versions are also available.

Note: The power consumption during power-start to output being stable (release operation) is 2 µ A greater than it is after that period (completion of release operation) because of delay circuit through current.

OPERATIONAL EXPLANATION

CMOS output

When a voltage higher than the release voltage (VDR) is applied to the voltage input pin (VIN), the voltage will gradually fall. When a voltage higher than the detect voltage (VDF) is applied to VIN, output (VOUT) will be equal to the input at VIN.

Note that high impedance exists at VOUT with the N-channel open drain configuration. If the pin is pulled up, VOUT will be equal to the pull up voltage.

When VIN falls below VDF, VOUT will be equal to the ground voltage (VSS) level (detect state). Note that this also applies to N-channel open drain configurations.

When VIN falls to a level below that of the minimum operating voltage (VMIN) output will become unstable. Because the output pin is generally pulled up with N-channel open drain configurations, output will be equal to pull up voltage. When VIN rises above the VSS level (excepting levels lower than minimum operating voltage), VOUT will be equal to VSS until VIN reaches the VDR level.

Although VIN will rise to a level higher than VDR, VOUT maintains ground voltage level via the delay circuit.

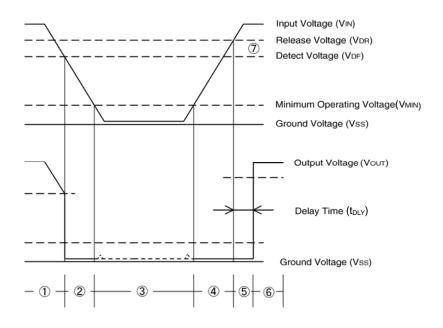
Following transient delay time, VIN will be output at VOUT. Note that high impedance exists with the N-channel open drain configuration and that voltage will be dependent on pull up.

Notes:

1. The difference between VDR and VDF represents the hysteresis range.

2. Release delay time (t_{DLY}) represents the time it takes for VIN to appear at VOUT once the said voltage has exceeded the VDR level.

Timing Chart



DIRECTIONS FOR USE

Notes on Use

- 1. Please use this IC within the stated maximum ratings. The IC is liable to malfunction should the ratings be exceeded.
- 2. When a resistor is connected between the VIN pin and the input with CMOS output configurations, oscillation may occur as a result of voltage drops at RIN if load current (IOUT) exists. It is therefore recommend that no resistor be added. (refer to Oscillation Description (1) below)
- 3. When a resistor is connected between the VIN pin and the input with CMOS output configurations, irrespective of N-ch output configurations, oscillation may occur as a result of through current at the time of voltage release even if load current (IOUT) does not exist. (refer to Oscillation Description (2) below)
- 4. With a resistor connected between the VIN pin and the input, detect and release voltage will rise as a result of the IC's supply current flowing through the VIN pin.
- 5. If a resistor (RIN) must be used, then please use with as small a level of input impedance as possible in order to control the occurrences of oscillation as described above.
 Eurther, please ensure that RIN is less than 10k, and that CIN is more than 0.1 u.E. (Figure 1). In such cases, detect

Further, please ensure that RIN is less than 10k and that CIN is more than 0.1μ F (Figure 1). In such cases, detect and release voltages will rise due to voltage drops at RIN brought about by the IC's supply current.

6. Depending on circuit's operation, transient delay time of this IC can be widely changed due to upper limits or lower limits of operational ambient temperature.

Oscillation Description

(1) Oscillation as a result of output current with the CMOS output configuration:

When the voltage applied at IN rises, release operations commence and the detector's output voltage increases. Load current (IOUT) will flow through RL. Because a voltage drop (RIN x IOUT) is produced at the RIN resistor, located between the input (IN) and the VIN pin, the load current will flow via the IC's VIN pin. The voltage drop will also lead to a fall in the voltage level at the VIN pin. When the VIN pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at RIN will disappear, the voltage level at the VIN pin will rise and release operations will begin over again.

Oscillation may occur with this " release - detect - release " repetition.

Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Oscillation as a result of through current:

Since the XC61F series are CMOS ICs, through current will flow when the IC's internal circuit switching operates (during release and detect operations). Consequently, oscillation is liable to occur during release voltage operations as a result of output current which is influenced by this through current (Figure 3). Since hysteresis exists during detect operations, oscillation is unlikely to occur.

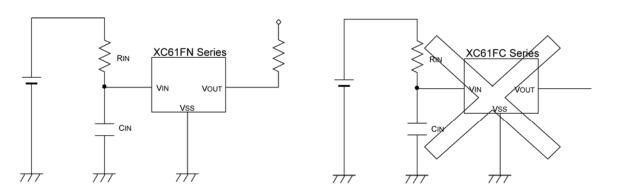


Figure 1. When using an input resistor

DIRECTIONS FOR USE (Continued)

Oscillation Description (Continued)

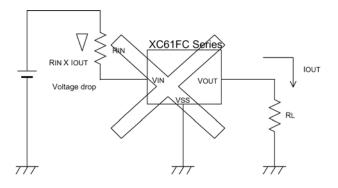


Figure 2. Oscillation in relation to output current

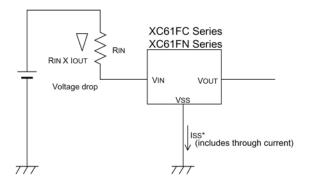
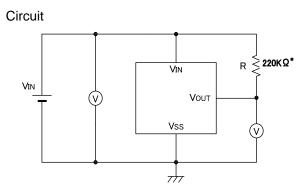


Figure 3. Oscillation in relation to through current

TEST CIRCUITS



Vin

Vss

777

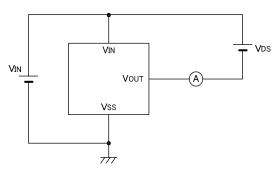
VOUT

(A)

VDS

Circuit

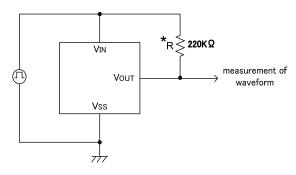




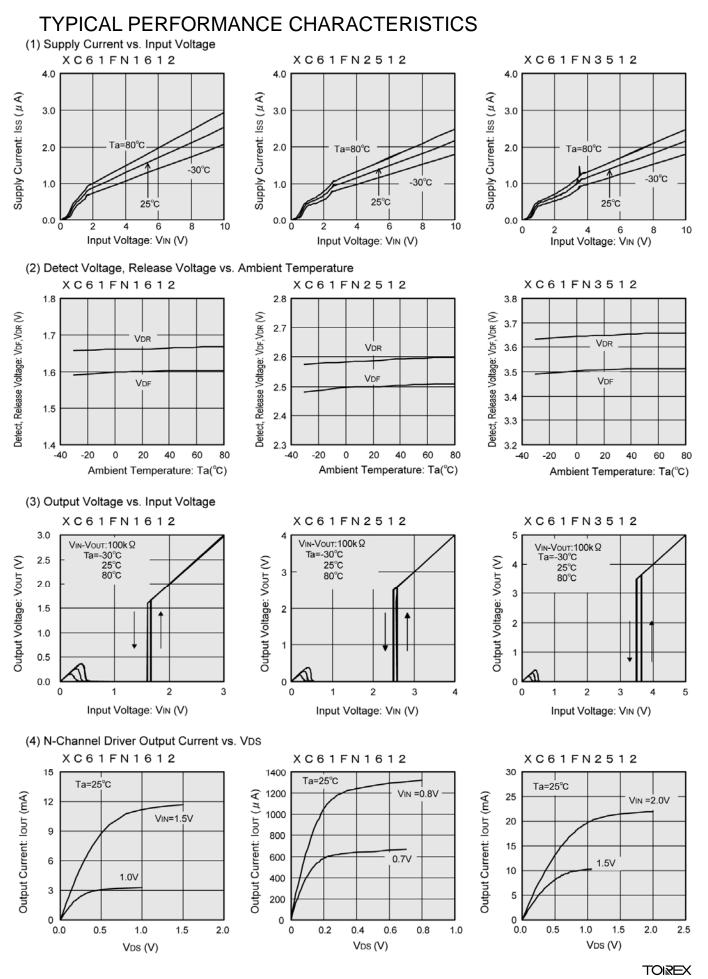
Circuit

Circuit

Vin

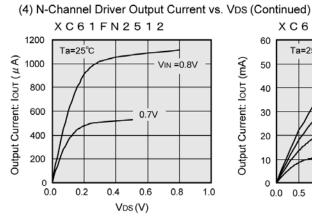


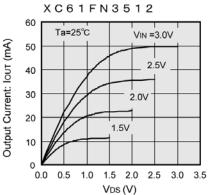
*Not necessary with CMOS output products.



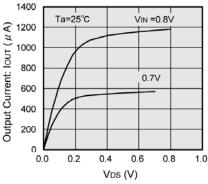
9/14

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

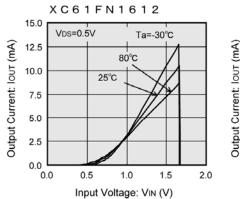


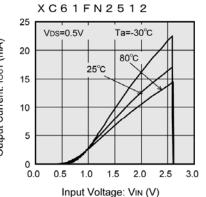






(5) N-Channel Driver Output Current vs. Input Voltage



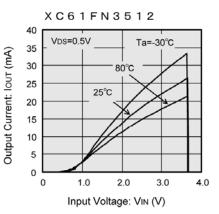


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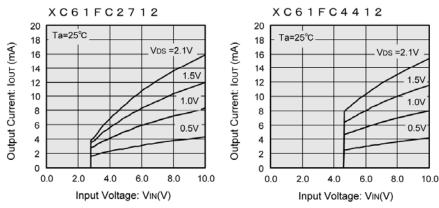
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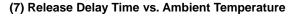
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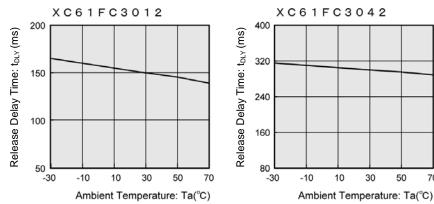
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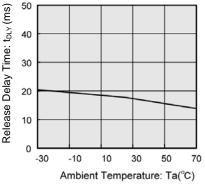
(6) P-Channel Driver Output Current vs. Input Voltage





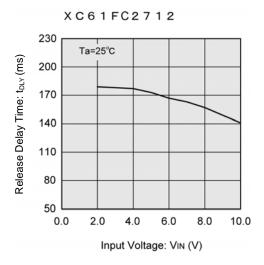






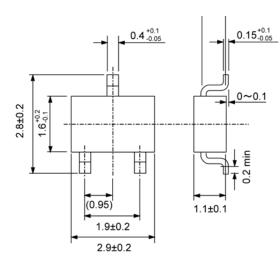
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

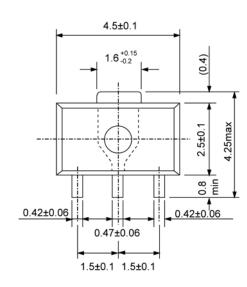
(8) Release Delay Time vs. Input Voltage



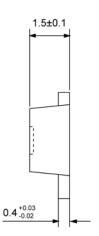
PACKAGING INFORMATION

SOT-23

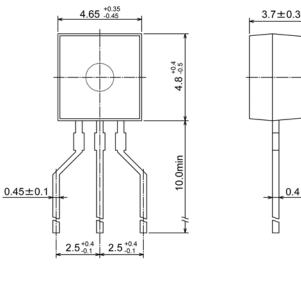


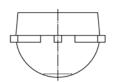


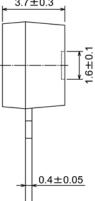
SOT-89



TO-92



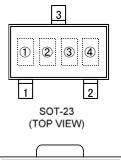


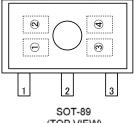


12/14

MARKING RULE

SOT-23, SOT-89





(TOP VIEW)

Represents integer of detect voltage and output configuration CMOS output (XC61FC series)

MARK	CONFIGURATION	VOLTAGE (V)
А	CMOS	0.x
В	CMOS	1.x
С	CMOS	2.x
D	CMOS	3.x
E	CMOS	4.x
F	CMOS	5.x
Н	CMOS	6.x
N-channel ope	en drain (XC61FN series)	
MARK	CONFIGURATION	VOLTAGE (V)
K	N-ch	0.x
L	N-ch	1.x
М	N-ch	2.x
N	N-ch	3.x
Р	N-ch	4.x
R	N-ch	5.x
S	N-ch	6.x

Represents decimal number of detect voltage

MARK	VOLTAGE (V)	MARK	VOLTAGE (V)
0	x.0	5	x.5
1	x.1	6	x.6
2	x.2	7	х.7
3	x.3	8	x.8
4	x.4	9	x.9

Represents delay time

VOLTAGE (V)	DELAY TIME
5	50 ~ 200ms
6	80 ~ 400ms
7	1 ~ 50ms

Represents assembly lot number (Based on internal standards)

Represents output configuration

MARK	OUTPUT CONFIGURATION
С	CMOS
N	N-ch

Represents detect voltage

MA	MARK	
		VOLTAGE (V)
3	3	3.3
5	0	5.0

Represents delay time

MARK	DELAY TIME
1	50ms ~ 200ms
4	80ms ~ 400ms
5	1ms ~ 50ms

Represents detect voltage accuracy

, , , , , , , , , , , , , , , , , , , ,	
MARK	DETECT VOLTAGE ACCURACY
2	Within <u>+</u> 2%

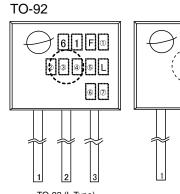
Represents a least significant digit of the production year (ex.)

MARK	PRODUCTION YEAR	
3	2003	
4	2004	

Represents production lot number

0 to 9, A to Z repeated (G, I, J, O, Q, W expected)

TOIREX 13/14



TO-92 (L Type) (TOP VIEW)

			(5
-	1	2		
	тс)-92 (P

F 1 5

7

I O-92 (T Type) (TOP VIEW)

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